

STTH3010-Y

Automotive ultrafast recovery - high voltage diode

Datasheet - production data

Features

- AEC-Q101 qualified
- Ultrafast soft recovery
- Very low conduction and switching losses
- High frequency and/or high pulsed current operation
- High reverse voltage capability
- High junction temperature
- ECOPACK[®]2 compliant component (STTH3010WY)

Description

The high quality design of this diode has produced a device with low leakage current, regularly reproducible characteristics and intrinsic ruggedness. These characteristics make it ideal for heavy duty applications that demand long term reliability like automotive applications.

The improved performance in low leakage current, and therefore thermal runaway guard band, is an immediate competitive advantage for this device.

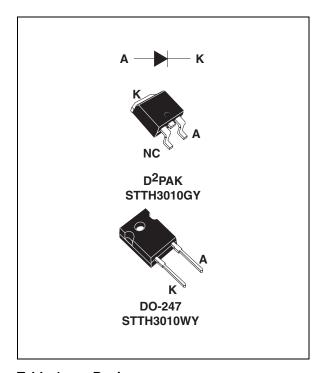


Table 1. Device summary

I _{F(AV)}	30 A
V _{RRM}	1000 V
T _j	175 °C
V _F (typ)	1.30 V
t _{rr} (typ)	42 ns

Characteristics STTH3010-Y

Characteristics 1

Absolute ratings (limiting values at 25 °C, unless otherwise specified) Table 2.

, , , , , , , , , , , , , , , , , , ,					
Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			1000	V
I _{F(RMS)}	Forward rms current	Forward rms current			Α
1	Average femuera ourrent S = 0.5	DO-247	T _c = 105 °C	20	Α
$I_{F(AV)}$ Average forward current, $\delta = 0.5$	D ² PAK	T _c = 105 °C	30	A	
I _{FRM}	Repetitive peak forward current	titive peak forward current $t_p = 5 \mu s$, $F = 5 kHz square$		300	Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms Sinusoidal}$		180	Α	
T _{stg}	Storage temperature range			-65 to +175	°C
Tj	Operating junction temperature range			-40 to +175	°C

Table 3. Thermal parameters

Symbol	Para	Value	Unit	
D	Junction to case	DO-247	4.4	°C/W
$R_{th(j-c)}$	Junction to case	D ² PAK	1.1	C/VV

Static electrical characteristics Table 4.

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _R = V _{RRM}			15	μΑ
IR Theverse leakage current	T _j = 125 °C	VR - VRRM		10	100	μΑ	
		T _j = 25 °C				2	
V _F ⁽²⁾ Forward voltage drop	T _j = 100 °C	I _F = 30 A		1.4	1.8	V	
		T _j = 150 °C			1.3	1.7	

^{1.} Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

To evaluate the conduction losses use the following equation: P = 1.3 x $I_{F(AV)}$ + 0.013 $I_{F}^{2}_{(RMS)}$

$$P = 1.3 \times I_{F(AV)} + 0.013 I_{F^2(BMS)}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

STTH3010-Y Characteristics

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Тур	Max.	Unit
		$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25 \text{ °C}$			100	
t _{rr}	Reverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = -100 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25 \text{ °C}$		53	70	ns
		$I_F = 1 \text{ A, } dI_F/dt = -200 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25 \text{ °C}$		42	55	
I _{RM}	Reverse recovery current	$I_F = 30 \text{ A}, \text{ d}I_F/\text{d}t = -200 \text{ A}/\mu\text{s}, \ V_R = 600 \text{ V}, T_j = 125 ^{\circ}\text{C}$		24	32	Α
S	Softness factor	$I_F = 30 \text{ A}, \text{ d}I_F/\text{d}t = -200 \text{ A}/\mu\text{s}, \ V_R = 600 \text{ V}, T_j = 125 ^{\circ}\text{C}$		1		
t _{fr}	Forward recovery time	$I_F = 30 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.5 \text{ x } V_{Fmax}, T_j = 25 \text{ °C}$			450	ns
V _{FP}	Forward recovery voltage	$I_F = 30 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s},$ $T_j = 25 ^{\circ}\text{C}$		5		V

Figure 1. Conduction losses versus average current

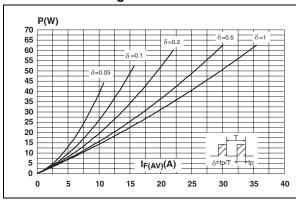


Figure 2. Forward voltage drop versus forward current

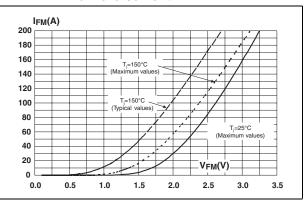
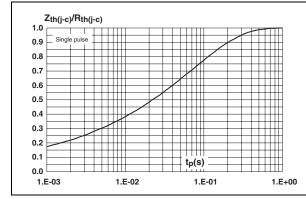
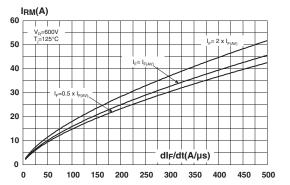


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values)





Characteristics STTH3010-Y

Figure 5. Reverse recovery time versus dl_F/dt (typical values)

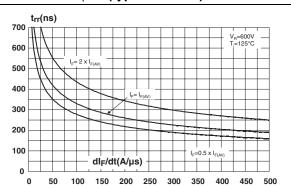


Figure 6. Reverse recovery charges versus dl_F/dt (typical values)

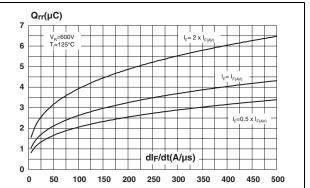
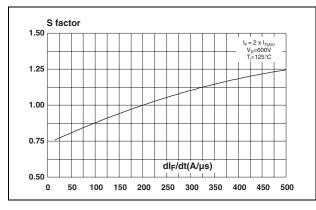
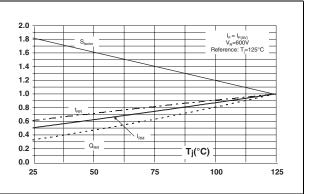


Figure 7. Softness factor versus dl_F/dt (typical values)

Figure 8. Relative variations of dynamic parameters versus junction temperature



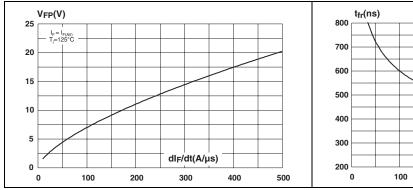


577

STTH3010-Y Characteristics

Figure 9. Transient peak forward voltage versus dl_F/dt (typical values)

Figure 10. Forward recovery time versus dI_F/dt (typical values)



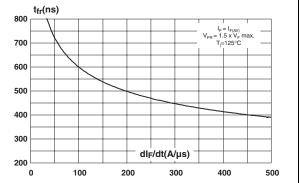
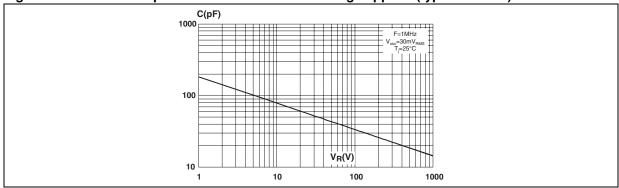


Figure 11. Junction capacitance versus reverse voltage applied (typical values)



2 Package information

Epoxy meets UL94, V0

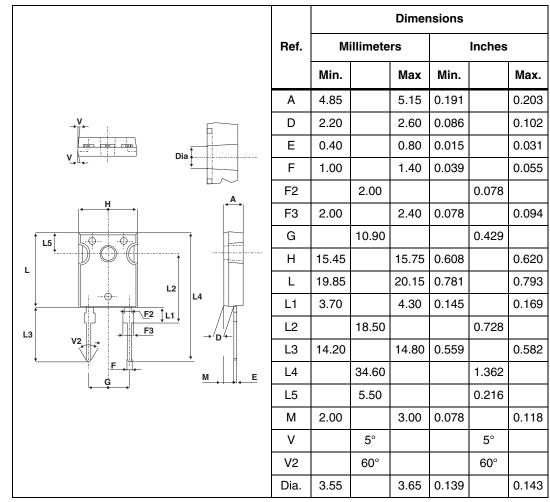
Cooling method: by conduction (C)

Recommended torque value: 0.80 N⋅m (DO-247)

Maximum torque value: 1.0 N⋅m (DO-247)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. DO-247 dimensions



STTH3010-Y Package information

Table 7. D²PAK dimensions

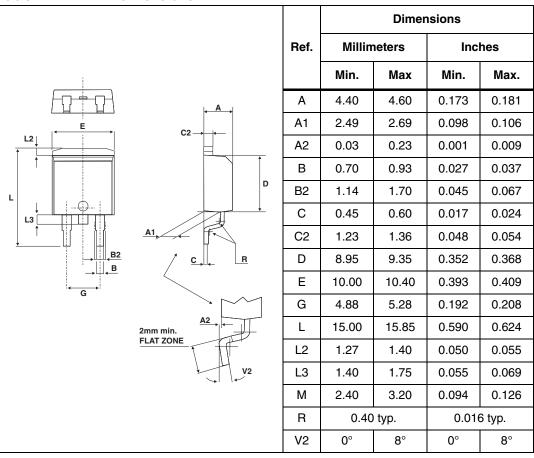
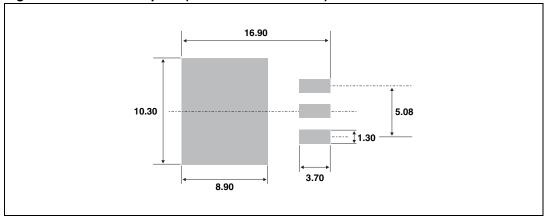


Figure 12. D²PAK footprint (all dimensions in mm)



Ordering information STTH3010-Y

3 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH3010WY	STTH3010WY	DO-247	4.4 g	30	Tube
STTH3010GY-TR	STTH3010GY	D ² PAK	1.49 g	1000	Tape and reel

4 Revision history

Table 9. Document revision history

Date	Revision	Description of Changes
28-Jun-2012	1	First issue.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

 $\ @\ 2012\ STM$ icroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

